



APPLICATION DATA SHEET

Electronic Version v14

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Title of Invention	METHOD OF FABRICATING LOW TEMPERATURE POLYSILICON THIN FILM TRANSISTOR		
Application Type : regular, utility Attorney Docket Number : TOPP0009USA			
Correspondence address: Customer Number: 027765			
			
Inventor Information: <u>Inventor 1:</u> Applicant Authority Type: Inventor Citizenship: TW Given Name: Hui-Chu Family Name: Lin Residence: City of Residence: Hsin-Chu Hsien Country of Residence: TW Address-1 of Mailing Address: 99-5, Shan-Chu-Hu, Chiu-Hu Tsun, Address-2 of Mailing Address: City of Mailing Address: Hsin-Chu Hsien State of Mailing Address: Postal Code of Mailing Address: Country of Mailing Address: TW Phone: Fax: E-mail:			
Attorney Information: practitioner(s) at Customer Number: 027765			
 as my attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.			